



SANYO Semiconductors

DATA SHEET

SR10300 Series — Ultrathin Miniature Package 1-channel Step-up DC/DC Converter ICs

Overview

The SR10300 Series is a SANYO's original SIP (System In Package) that includes a DC/DC converter control IC, a power MOSFET and a Schottky barrier diode. All these components are mounted into one thin-and-small package by utilizing SANYO's high-density mounting technology, "Integrated System in Board (ISB)".

The advantage using this DC/DC converter package is that it greatly decreases its mounting area and space, compared with when the same circuit is set up with the discrete devices. In addition to that, it is very easy to assemble step-up switching power supply with by just adding voltage-setting resistance, inductor and capacitors.

Functions and Features

- Since the SR10300 Series packages a voltage step-up DC/DC converter IC as well as power MOSFET and Schottky barrier diode devices in the same package with the minimum trace length between components, it can provides high efficiency and superior characteristics including low output ripple. In particular the mounting area required by these components is reduced when compared to implementations using discrete devices.
- The output voltage is set using an external resistor.
- Standby function: Standby mode current=1 μ A (maximum)
- External PWM/PFM switching control
- Oscillator frequency: 100kHz (SR10310), 180kHz (SR10320), 300kHz (SR10330) (accuracy \pm 15%)

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SR10300 Series

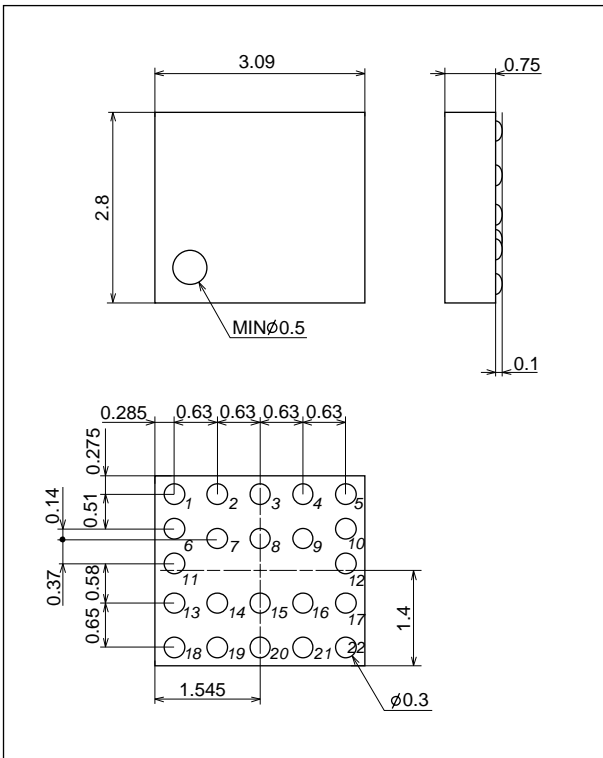
Comparison of Functions

Type No.	DC/DC Controller IC			TR Maximum Rating		Di Maximum Rating		Output Setting *1
	Control System	Input Voltage Range	Oscillator Frequency	V_{DSS}	I_D	V_{RRM}	I_O	
SR10310	External PWM/PFM switching control	0.9V to 10V	100kHz	20V	3A	30V	1A	1.5V to 13V
SR10320	External PWM/PFM switching control	0.9V to 10V	180kHz	20V	3A	30V	1A	1.5V to 13V
SR10330	External PWM/PFM switching control	0.9V to 10V	300kHz	20V	3A	30V	1A	1.5V to 13V

*1: The output setting maximum values are voltages that are 1/1.5 times the V_{DSS} and V_{RRM} as a general rule of thumb, and they are provided to serve as a reference only. As such, it must be verified during actual operation that they do not exceed the rated voltages.

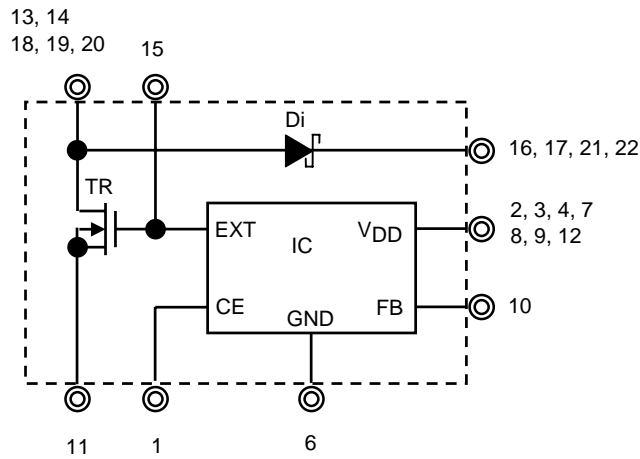
Package Dimensions

unit : mm



SR10300 Series

Pin Layout and Internal Equivalent Circuit Block Diagram



Specifications

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

Device	Parameter	Symbol	Conditions	Ratings	Unit
IC	V_{DD} pin voltage	V_{DD}		-0.3 to +12	V
	FB pin voltage	V_{FB}		-0.3 to +12	V
	CE pin voltage	V_{CE}		-0.3 to +12	V
	EXT pin voltage	V_{EXT}		-0.3 to $V_{DD}+0.3$	V
	EXT pin current	I_{EXT}		± 100	mA
TR	Drain-to-source voltage	V_{DSS}		20	V
	Gate-to-source voltage	V_{GSS}		± 10	V
	Drain current	I_D		3	A
	Allowable power dissipation	P_{D-T}	60mm×60mm×1.6mm ³ FR4 board	TBD	mW
Di	Reverse voltage	V_{RRM}		30	V
	Output current	I_O		1	A
	Allowable power dissipation	P_{D-D}	60mm×60mm×1.6mm ³ FR4 board	TBD	mW
Operating temperature		T_{opr}		-30 to +85	$^\circ\text{C}$
Storage temperature		T_{stg}		-40 to +125	$^\circ\text{C}$

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Electrical Characteristics

Overall Operating Characteristics at $T_a = 25^\circ\text{C}$, in the specified test circuit

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Output voltage	V_{OUT}	$V_{IN}=2\text{V}, I_O=10\text{mA}$	3.217	3.300	3.383	V
Output voltage setting range	VOSET	$V_{IN}=\text{VOSET} \times 0.6, V_{DD}=3.3\text{V}, I_{OUT}=10\text{mA}$	1.5		13 *2	V
FB control voltage	VFB			0.9		V
Supply voltage	V_{DD}	*3	1.8		10	V
Operation start voltage	VST	$I_O=1\text{mA}$			0.9	V
Current dissipation	I_{DD}	$V_{IN}=2\text{V}, I_O=0\text{mA}$ SR10310		29	41	μA
		$V_{IN}=2\text{V}, I_O=0\text{mA}$ SR10320		45	64	μA
		$V_{IN}=2\text{V}, I_O=0\text{mA}$ SR10330		62	88	μA
Standby current	ISTB	$V_{IN}=2\text{V}, V_{CE}=0\text{V}$			1	μA
Oscillator frequency	FOSC	$V_{IN}=2\text{V}, I_O=10\text{mA}$ SR10310	85	100	115	kHz
		$V_{IN}=2\text{V}, I_O=10\text{mA}$ SR10320	153	180	207	kHz
		$V_{IN}=2\text{V}, I_O=10\text{mA}$ SR10330	255	300	345	kHz
Efficiency	EFFI			81		%
CE high voltage	VCEH		0.65			V
CE low voltage	VCEL				0.20	V
PWM high voltage	VPWMH	*4	$V_{DD}-0.2$			V
PWM low voltage	VPWML	*4			$V_{DD}-1.0$	V
CE high current	ICEH	$CE=V_{DD}=3.3\text{V}$			0.1	μA
CE low current	ICEL	$CE=0\text{V}$			0.1	μA

- *2: The output setting maximum voltages are within 1/1.5 times the V_{DSS} of the built-in MOSFET and within 1/1.5 times the V_{RRM} of the Di as a general rule of thumb. As such, it must be verified during actual operation that they do not exceed the rated voltages.
- *3: V_{DD} should be 1.8V or higher when V_{IN} or other power source is supplying V_{DD} since the output voltage and oscillating frequency become steady when V_{DD} is set 1.8V or higher, although the built-in IC starts step-up voltage operation from $V_{DD}=0.8\text{V}$.
- *4: The CE pin also serves to implement a PWM/PFM external switching function. When the voltage is $V_{DD}-0.2\text{V}$ or more, PWM control is exercised, and when it is VCEH or more but $V_{DD}-1.0\text{V}$ or less, PWM/PFM automatic switching at a duty ratio of 25% is controlled.

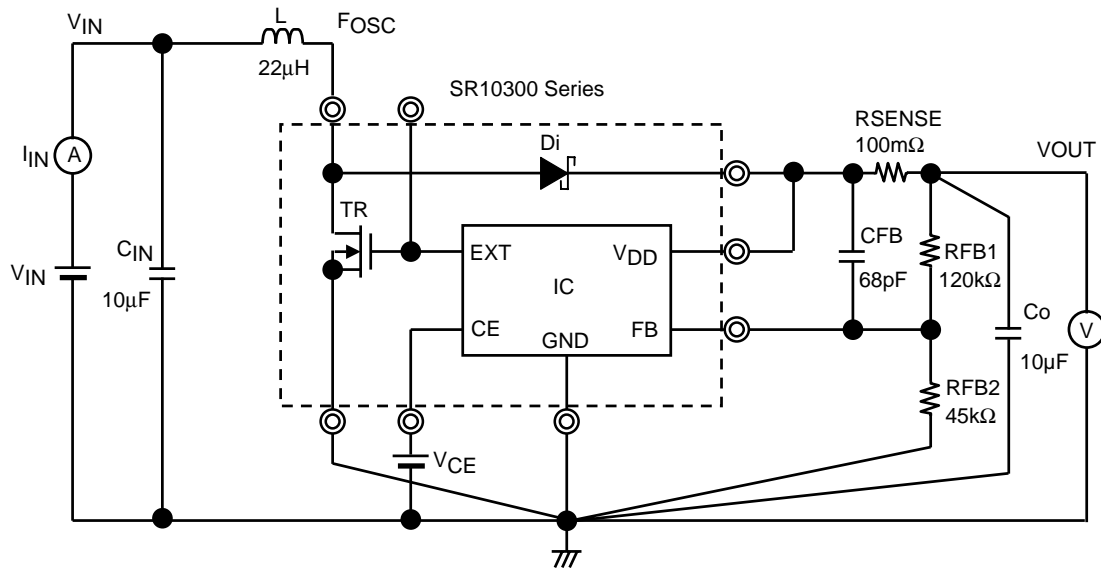
Di Characteristics at $T_a = 25^\circ\text{C}$, in the specified test circuit

Parameter	Symbol	Conditions	min	typ	max	unit
Forward voltage	VF	$I_F=1\text{A}$		0.43	0.47	V
Reverse current	IR	$V_R=30\text{V}$		40	200	μA

Pin Functions

Pin No.	Pin Name	Description
1	IC CE/PWM	Operation starts when chip-enable pin is set "High". This pin also serves as a PWM/PFM selector.
2, 3, 4, 7, 8, 9, 12	IC V_{DD}	Supply voltage for IC
5	NC	
6	GND	Ground pin for IC
10	IC FB	External resistance connecting pin for output voltage setting, internal control voltage: 0.9V typical
11	TR Source	Source pin for TR
13, 14, 18,19, 20	TR Drain, Di Anode	Drain of TR and Anode of Diode
15	IC EXT, TR Gate	Gate for TR
16, 17, 21, 22	Di Cathode	Cathode of Diode and V_{OUT}

Equivalent Circuit and Test Peripheral Circuitry



Selection rules of external components

- 1) RFB: Set the ratio of RFB1 and RFB2 to be $R_{FB1} + R_{FB2} \leq 2M\Omega$ and $V_{FB} = 0.9V$.
- 2) CFB: Set $f_{zfb} = 1 / (2 \times \pi \times C_{FB} \times R_{FB1})$ to be within 5kHz to 30kHz.
- 3) L, C_O, R_{SENSE}:

- | | |
|--|---|
| When ceramic capacitor is used for C _O : | L=10µH, C _O =10µF (SR10330) |
| | L=22µH, C _O =10µF (SR10310, SR10320) |
| | R _{SENSE} =50mΩ (SR10310), 100mΩ (SR10320, SR10330) |
| When tantalum capacitor is used for C _O : | L=22µH, C _O =47µF (SR10330) |
| | L=47µH, C _O =47µF (SR10310, SR10320) |
| | R _{SENSE} =None (shorted) |
| When electrolytic capacitor is used for C _O : | L=22µH, C _O =100µF//2.2µF ceramic (SR10330) |
| | L=47µH, C _O =100µF//2.2µF ceramic (SR10310, SR10320) |
| | R _{SENSE} =None (shorted) |

These constants of the components above should be changed if necessary for larger step-up ratio V_{OUT}/V_{IN} and larger output current I_{OUT} using the expression shown below as a reference.

$$C_O = (\text{Standard } C_O^*) \times (I_{OUT} \text{ (mA)} / 300\text{mA}) \times V_{OUT}/V_{IN}$$

* Standard C_O: values shown above

<Manufactured by>

ISB Business Unit, Electronic Device Company,
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